

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claim 1 (Currently Amended): A method for manufacturing a semiconductor device comprising ~~the steps of:~~

~~forming an insulating region for a first insulating an active region formed in a semiconductor layer formed on a semiconductor substrate through the first insulating layer;~~

forming a semiconductor layer on said first insulating layer;

forming an insulating region on said first insulating layer to insulate said semiconductor layer;

forming a conductive layer on said semiconductor layer after forming said insulating region; and

implanting ions in said semiconductor layer after forming said conductive layer, thereby forming ~~[[said]]~~ an active region within said semiconductor layer.

Claim 2 (Original): A method as claimed in claim 1 wherein said conductive layer is made of carbon (C).

Claim 3 (Original): A method as claimed in claim 2 wherein said conductive layer has a thickness of 5nm to 10nm.

Claim 4 (Original): A method as claimed in claim 1 wherein said conductive layer is made of silicon (Si) doped with impurity ions.

Claim 5 (Original): A method as claimed in claim 4 wherein said conductive layer has a thickness of 5nm to 10nm.

Claim 6 (Original): A method as claimed in claim 1 wherein said conductive layer is made of an arbitrary metal selected from a metal group including gold (Au), an Au-alloy, platinum (Pt), a Pt-alloy, and an alloy of Au and Pt.

Claim 7 (Original): A method as claimed in claim 6 wherein said conductive layer has a thickness of 1nm to 5nm.

Claim 8 (Original): A method as claimed in claim 1 wherein said conductive layer is made of aluminum (Al) or an Al-alloy.

Claim 9 (Original): A method as claimed in claim 8 wherein said conductive layer has a thickness of 1nm to 5nm.

Claim 10 (Currently Amended): A method as claimed in claim 1 further comprising a ~~step of forming a~~ [[the]] second insulating layer on said semiconductor layer in [[on]] which said active region is formed.

Claim 11 (Original): A method as claimed in claim 10 wherein said conductive layer is made of carbon (C).

Claim 12 (Original): A method as claimed in claim 11 wherein said conductive layer has a thickness of 5nm to 10nm.

Claim 13 (Original): A method as claimed in claim 10 wherein said conductive layer is made of silicon (Si) doped with impurity ions.

Claim 14 (Original): A method as claimed in claim 13 wherein said conductive layer has a thickness of 5nm to 10nm.

Claim 15 (Original): A method as claimed in claim 10 wherein said conductive layer is made of an arbitrary metal selected from a metal group including gold (Au), an Au-alloy, platinum (Pt), a Pt-alloy, and an alloy of Au and Pt.

Claim 16 (Original): A method as claimed in claim 15 wherein said conductive layer has

a thickness of 1nm to 5nm.

Claim 17 (Original): A method as claimed in claim 10 wherein said conductive layer is made of aluminum (Al) or an Al-alloy.

Claim 18 (Original): A method as claimed in claim 17 wherein said conductive layer has a thickness of 1nm to 5nm.

Claim 19 (Currently Amended): A method as claimed in claim 1 further comprising the steps of:

removing said conductive layer after forming said active region implanting ions;

and

forming ~~[[the]]~~ a second insulating layer on said active region of said semiconductor layer after removing said conductive layer.

Claim 20 (Original): A method as claimed in claim 19 wherein said conductive layer is made of carbon (C).

Claim 21 (Original): A method as claimed in claim 20 wherein said conductive layer has a thickness of 5nm to 10nm.

Claim 22 (Original): A method as claimed in claim 19 wherein said conductive layer is made of silicon (Si) doped with impurity ions.

Claim 23 (Original): A method as claimed in claim 2 wherein said conductive layer has a thickness of 5nm to 10nm.

Claim 24 (Original): A method as claimed in claim 1 wherein said conductive layer is made of an arbitrary metal selected from a metal group including gold (Au), an Au-alloy, platinum (Pt), a Pt-alloy, and an alloy of Au and Pt.

Claim 25 (Original): A method as claimed in claim 24 wherein said conductive layer has a thickness of 1nm to 5nm.

Claim 26 (Original): A method as claimed in claim 19 wherein said conductive layer is made of aluminum (Al) or an Al-alloy.

Claim 27 (Original): A method as claimed in claim 26 wherein said conductive layer has a thickness of 1nm to 5nm.